BORN SEMICONDUCTOR

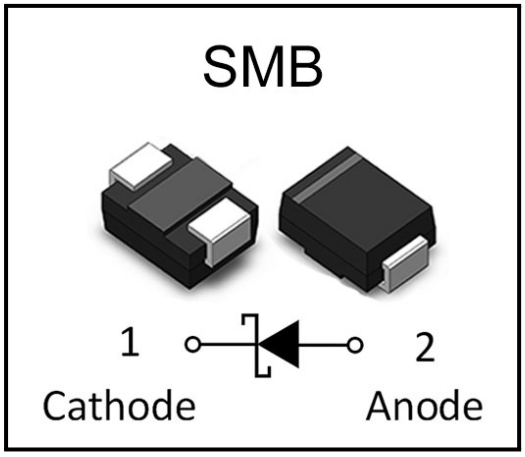
SS32-SS320

Schottky Barrier Diode

Features

- For surface mounted applications
- Matal silicon junction,majority carrier conduction
- Low power loss,high efficiency
- Buit-in strain relief,ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

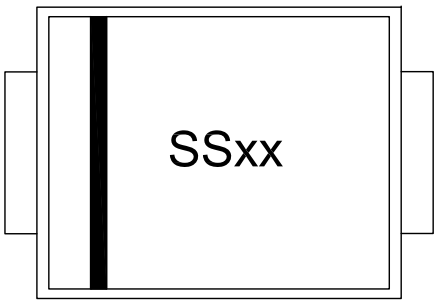
Package



Description

- Case: JEDEC DO-214AA molded plastic
- Terminals:Axial leads.Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position:Any

Marking



Ordering information

Part Number	SS32	SS33	SS34	SS35	SS36	SS38	SS310	SS315	SS320
Marking	SS32	SS33	SS34	SS35	SS36	SS38	SS310	SS315	SS320
Base qty	3K	3K	3K	3K	3K	3K	3K	3K	3K

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SS32-SS320

Schottky Barrier Diode

Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS 32	SS 33	SS 34	SS 35	SS 36	SS 38	SS 310	SS 315	SS 320	Units
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	20	30	40	50	60	80	100	150	200	V
V_{RMS}	Maximum RMS Reverse Voltage	14	21	28	35	42	56	70	105	140	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	100	150	200	V
$I_{F(AV)}$	Maximum Average Forward Rectified	3.0									A
I_{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	80									A
V_F	Maximum Forward Voltage at 3.0A DC	0.55			0.70		0.85		0.95		V
I_R	Maximum Reverse current T_A=25°C	0.50					0.10				mA
	at Rated DC Blocking Voltage T_A=100°C	10					5				
C_J	Typical Junction Capacitance	250									pF
T_J	Operating Temperature Range	-55 to +150									°C
T_{STG}	Storage Temperature Range	-55 to +150									°C
$R_{\theta JA}$	Thermal Resistance(1)	55									°C/W
$R_{\theta JL}$		20									

Note:(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6” x 0.6” (16 mm x 16mm) copper pad areas

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Typical Performance Characteristics(T_J = 25 °C, unless otherwise noted)

Figure 1:I_O-T_C Curve

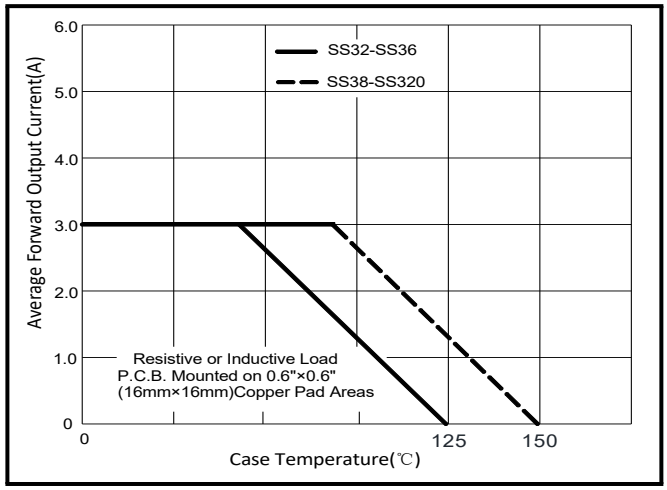


Figure 2:Surge Forward Current Capability

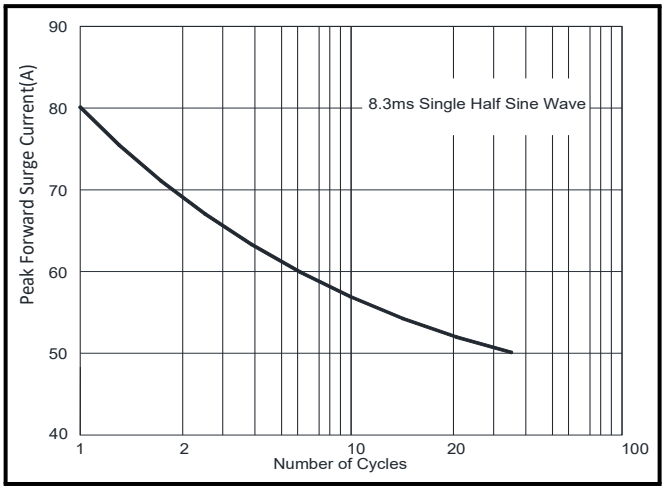


Figure 3:Forward Voltage

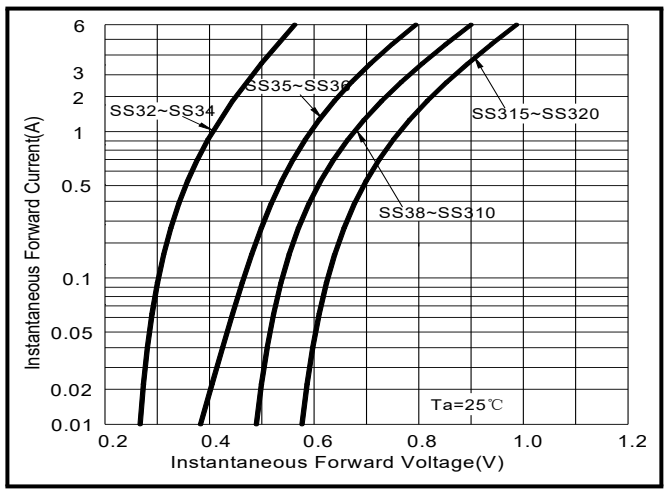
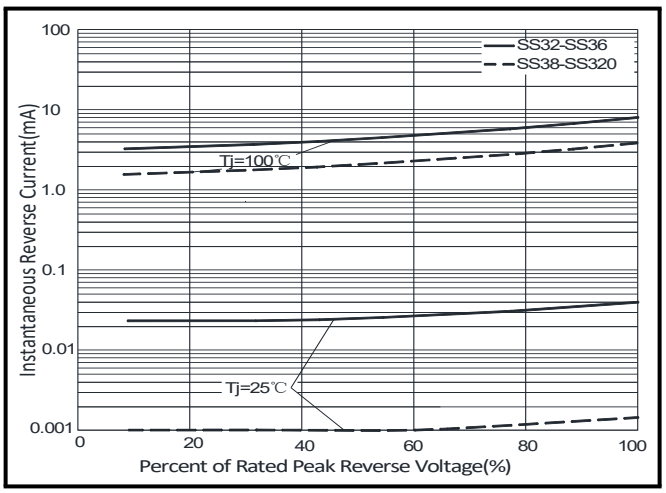


Figure 4:Typical Reverse Characteristics



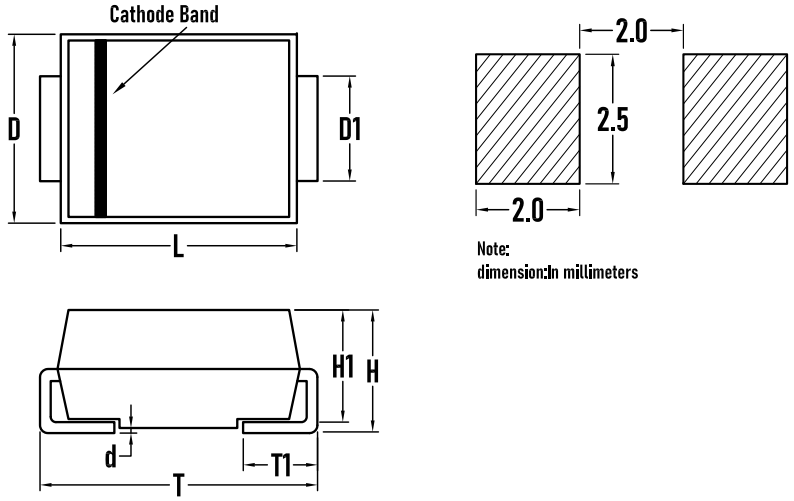
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SS32-SS320

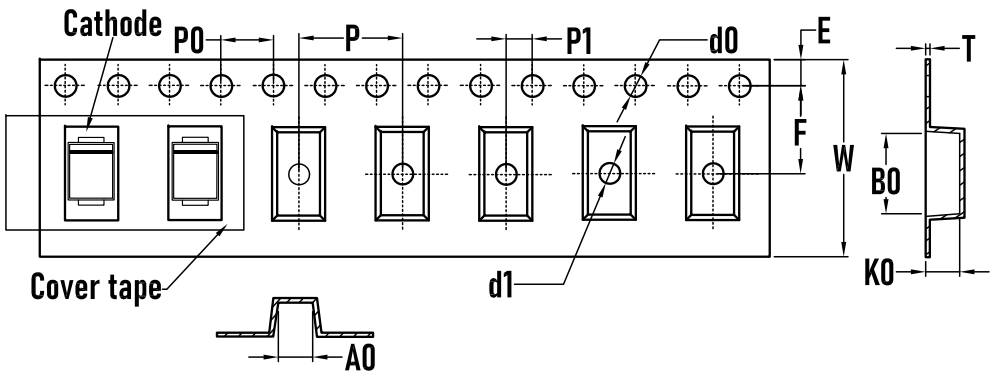
Schottky Barrier Diode

Outline Drawing - SMB



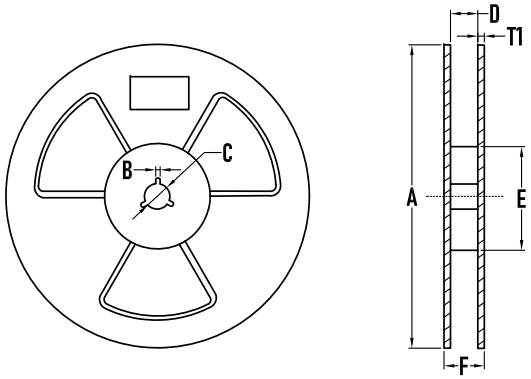
SYMBOL	MILLIMETER		Inches	
	MIN.	MAX.	MIN.	MAX.
D	3.3	3.9	0.130	0.154
D1	1.7	2.3	0.067	0.091
T	5.1	5.7	0.201	0.224
T1	0.8	1.6	0.031	0.063
d	–	0.3	–	0.012
H1	2.0	2.4	0.079	0.094
H	2.1	2.5	0.083	0.098
L	4.0	4.7	0.157	0.185

Packaging Tape - SMB



SYMBOL	MILLIMETER
A0	3.60±0.1
B0	5.45±0.1
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	5.50±0.1
K0	2.30±0.1
P	8.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	12.00±0.1
T	0.22±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	13±2
E	73±2
T1	2.2±0.2
Quantity	3000PCS

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Revision: 2022-Jan-1-A